



钜地半导体
Tudi Semiconductor

Product Specification

AT24C02C-PUM-TUDI

I²C-Compatible(2-wire)Serial EEPROM
1-Kbit(128*8)or 2-Kbit(256*8)

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**semiconductor device
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- Design
- research and development
- production
- and sales



Features

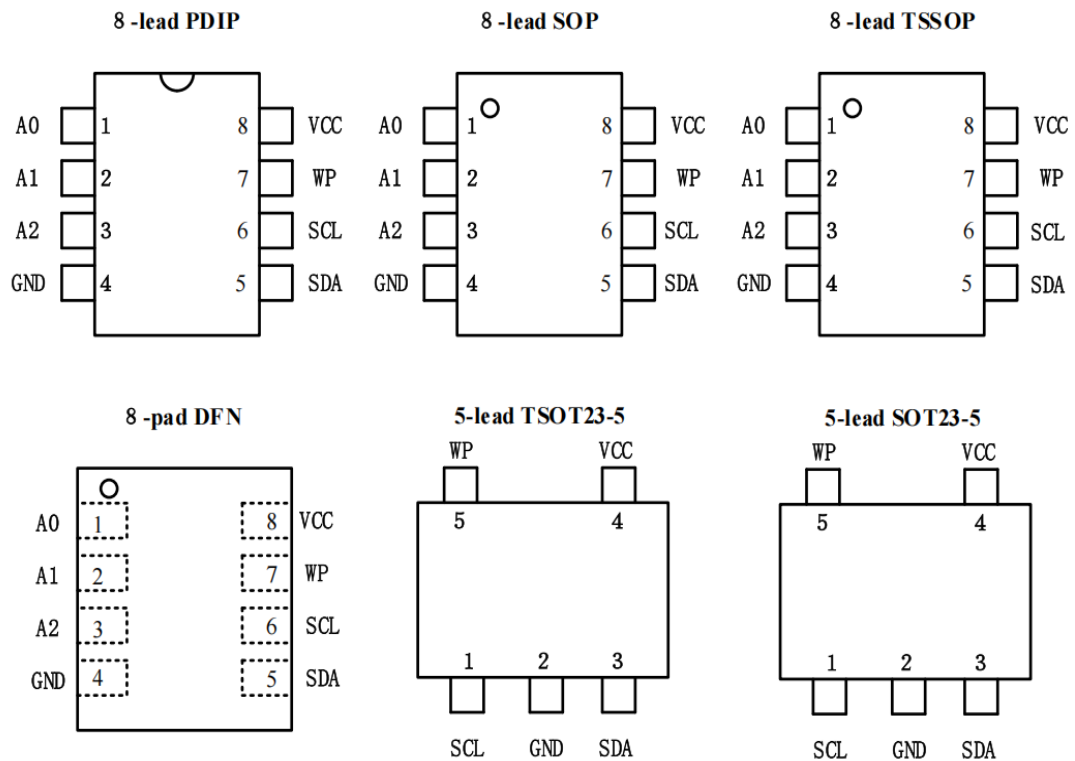
- Low voltage operation
 - 1.7V ($V_{CC} = 1.7V$ to 3.6V)
- Internally organized 128 x 8 (1K) or 256 x 8 (2K)
- I²C-Compatible (2-wire) serial interface
- Schmitt Triggers, filtered inputs for noise suppression
- Bidirectional data transfer protocol
- Write Protect pin for full array hardware data protection
- 8-byte Page Write mode
 - Partial page writes allowed
- Random and Sequential Read modes
- High reliability
 - Endurance: 1,000,000 write cycles
 - Data retention: 100 years
- Green package options (Lead-free/Halide-free/RoHS Compliant)
 - 8-lead SOIC, 8-lead TSSOP, 8-pad UDFN, 8-lead PDIP, ⁽¹⁾ 5-lead SOT23, and 8-ball VFBGA
- Die sale options: wafer form and tape and reel available

Description

The AT24C01/02 provides 1,024/2,048 bits of Serial Electrically Erasable and Programmable Read-Only Memory (EEPROM) organized as 128/256 words of eight bits each. The device's cascadable feature allows up to eight devices to share a common 2-wire bus. These device are optimized for use in many industrial and commercial applications where low-power and low-voltage operation are essential. Both devices are available in space-saving 8-lead SOIC, 8-lead TSSOP, 8-pad UDFN, 8-lead PDIP, ⁽¹⁾ 5-lead SOT23, and 8-ball VFBGA packages.



Pin Configuration



Pin Descriptions

Pin Name	Type	Functions
A0-A2	I	Address Inputs
SDA	I/O	Serial Data
SCL	I	Serial Clock Input
WP	I	Write Protect
GND	P	Ground
Vcc	P	Power Supply

Table 1

Block Diagram

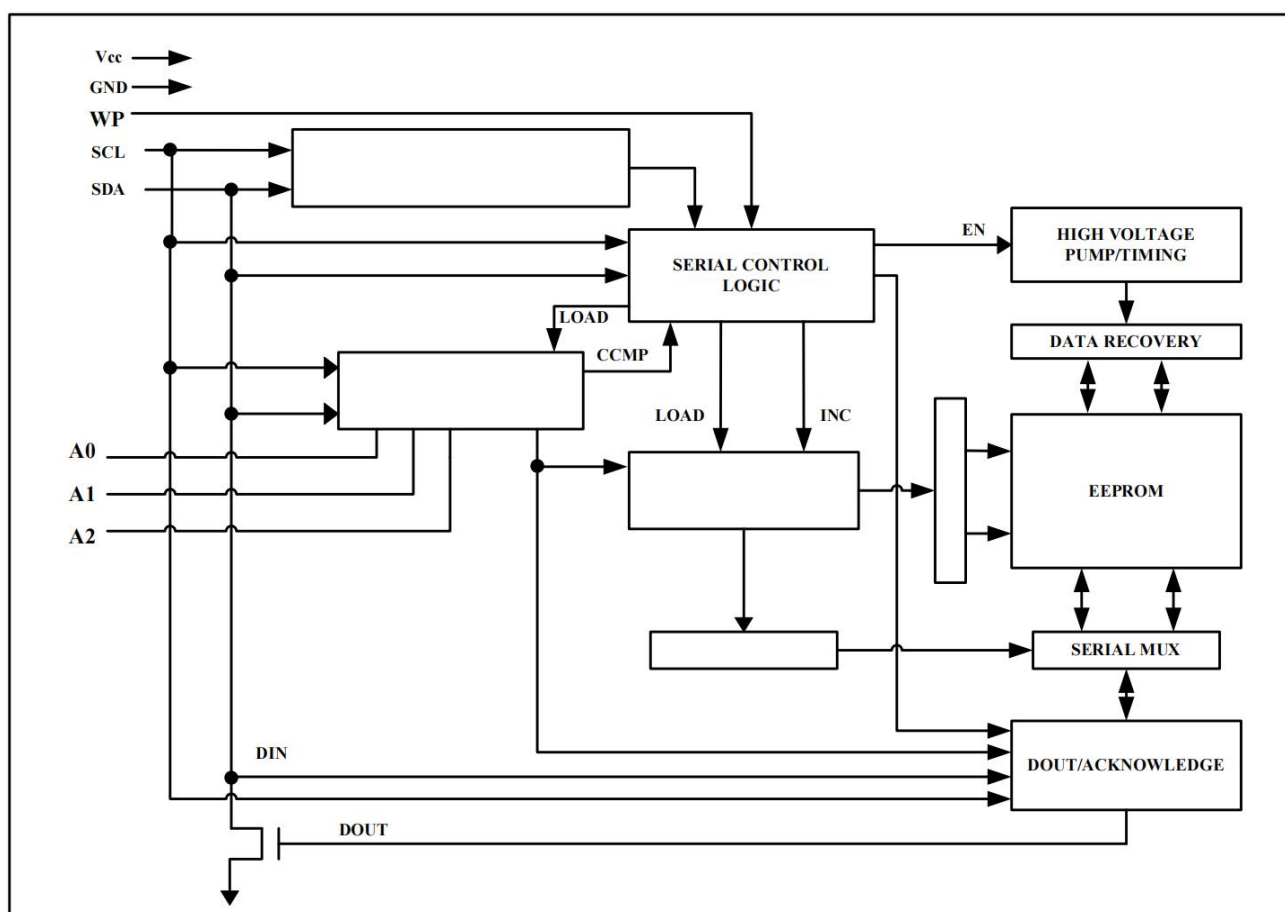


Figure 1

DEVICE/PAGE ADDRESSES (A2, A1 and A0): The A2, A1 and A0 pins are device address inputs that are hard wire for the 24C01/24C02 . Eight 2K devices may be addressed on a single bus system (device addressing is discussed in detail under the Device Addressing section).

SERIAL DATA (SDA): The SDA pin is bi-directional for serial data transfer. This pin is open-drain driven and may be wire-ORed with any number of other open-drain or open-collector devices.

SERIAL CLOCK (SCL): The SCL input is used to positive edge clock data into each EEPROM device and negative edge clock data out of each device.

WRITE PROTECT (WP): The 24C01/24C02 has a Write Protect pin that provides hardware data protection. The Write Protect pin allows normal read/write operations when connected to ground (GND). When the Write Protection pin is connected to Vcc, the write protection feature is enabled and operates as shown in the following **Table 2**.



WP Pin Status	24C01/24C02
At VCC	Full(2K) Array
At GND	Normal Read/Write Operations

Table 2

Functional Description

1. Memory Organization

24C01/24C02, 2K SERIAL EEPROM: Internally organized with 16 pages of 16 bytes each, the 2K requires a 8-bit data word address for random word addressing.

2. Device Operation

CLOCK and DATA TRANSITIONS: The SDA pin is normally pulled high with an external device. Data on the SDA pin may change only during SCL low time periods (see **Figure 2**). Data changes during SCL high periods will indicate a start or stop condition as defined below.

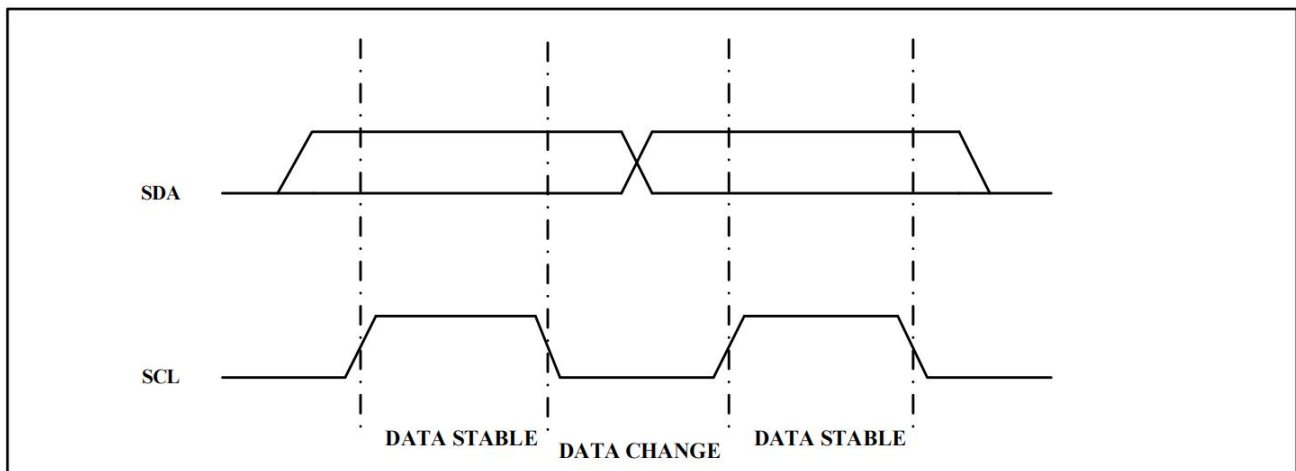


Figure 2. Data Validity

START CONDITION: A high-to-low transition of SDA with SCL high is a start condition which must precede any other command (see **Figure 3**).

STOP CONDITION: A low-to-high transition of SDA with SCL high is a stop condition. After a read sequence, the stop command will place the EEPROM in a standby power mode (see **Figure 3**).

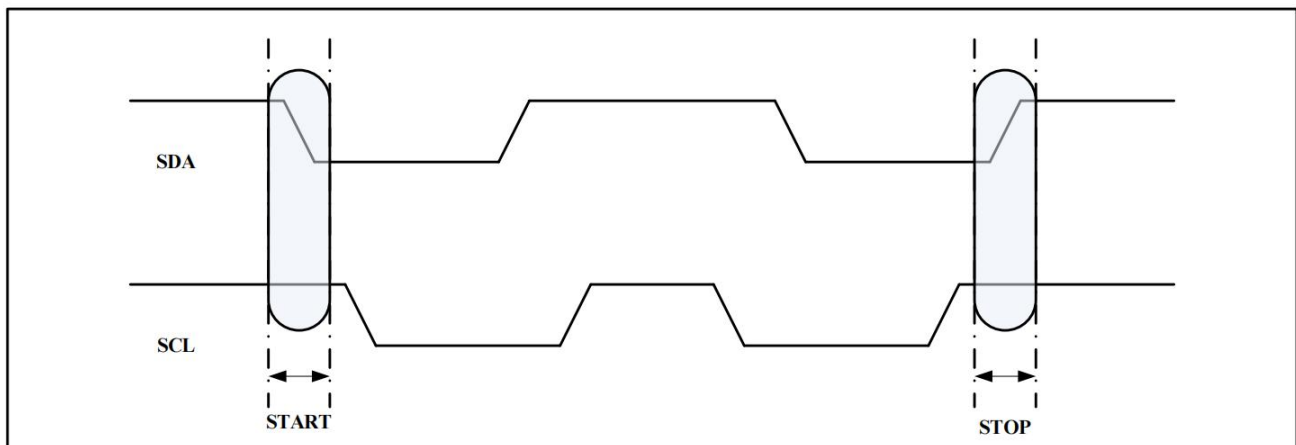


Figure 3. Start and Stop Definition



ACKNOWLEDGE: All addresses and data words are serially transmitted to and from the EEPROM in 8-bit words. The EEPROM sends a "0" to acknowledge that it has received each word. This happens during the ninth clock cycle.

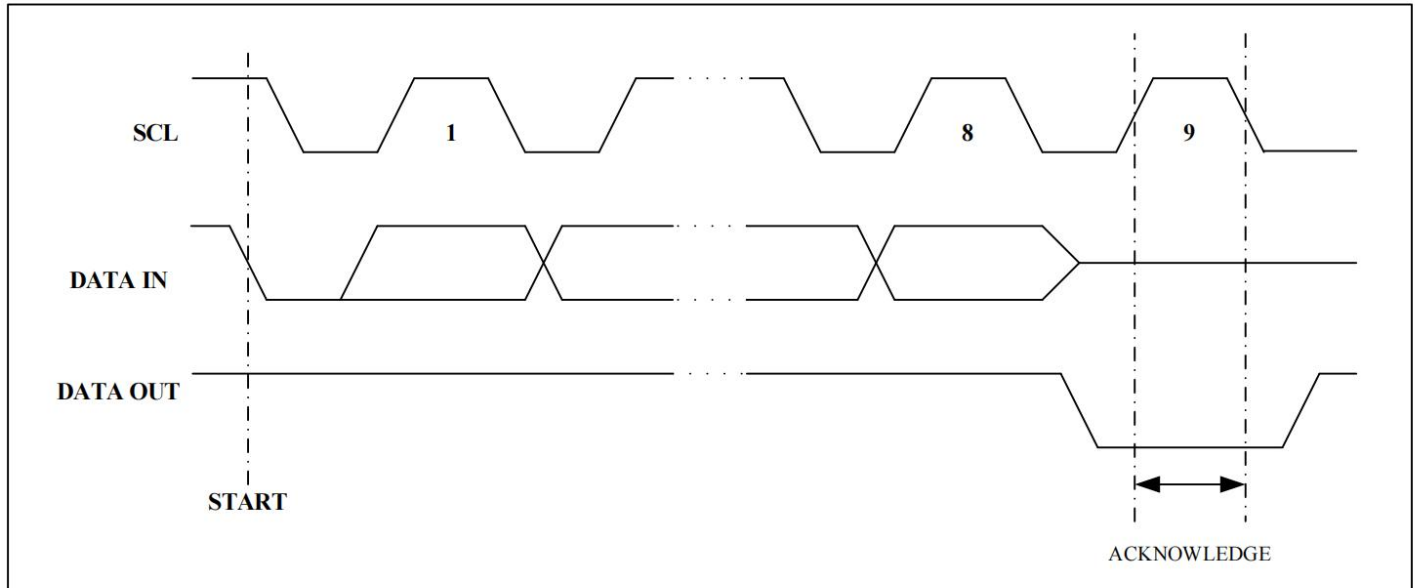


Figure 4. Output Acknowledge

STANDBY MODE: The 24C01/24C02 features a low-power standby mode which is enabled: (a) upon power-up and (b) after the receipt of the STOP bit and the completion of any internal operations.

MEMORY RESET: After an interruption in protocol, power loss or system reset, any two-wire part can be reset by following these steps:

1. Clock up to 9 cycles.
2. Lock SDA high in each cycle while SCL is high.
3. Create a start condition.



3. Device Addressing

The 2K EEPROM devices all require an 8-bit device address word following a start condition to enable the chip for a read or write operation (see **Figure 5**)

MSB				LSB			
1	0	1	0	A2	A1	A0	R/W

Figure 5. Device Address

The device address word consists of a mandatory "1", "0" sequence for the first four most significant bits as shown. This is common to all the Serial EEPROM devices.

The 2K EEPROM uses A2, A1 and A0 device address bits to allow as much as eight devices on the same bus. These 3 bits must be compared to their corresponding hardwired input pins. The A2, A1 and A0 pins use an internal proprietary circuit that biases them to a logic low condition if the pins are allowed to float.

The eighth bit of the device address is the read/write operation select bit. A read operation is initiated if this bit is high and a write operation is initiated if this bit is low.

Upon a compare of the device address, the EEPROM will output a "0". If a compare is not made, the chip will return to a standby state.

DATA SECURITY: The 24C01/24C02 has a hardware data protection scheme that allows the user to write protect the entire memory when the WP pin is at VCC.

4. Write Operations

BYTE WRITE: A write operation requires an 8-bit data word address following the device address word and acknowledgment. Upon receipt of this address, the EEPROM will again respond with a "0" and then clock in the first 8-bit data word. Following receipt of the 8-bit data word, the EEPROM will output a "0" and the addressing device, such as a microcontroller, must terminate the write sequence with a stop condition. At this time the EEPROM enters an internally timed write cycle, t_{WR} , to the nonvolatile memory. All inputs are disabled during this write cycle and the EEPROM will not respond until the write is complete (see **Figure 7**).

B7	B6	B5	B4	B3	B2	B1	B0
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Figure 6. ADDRESS

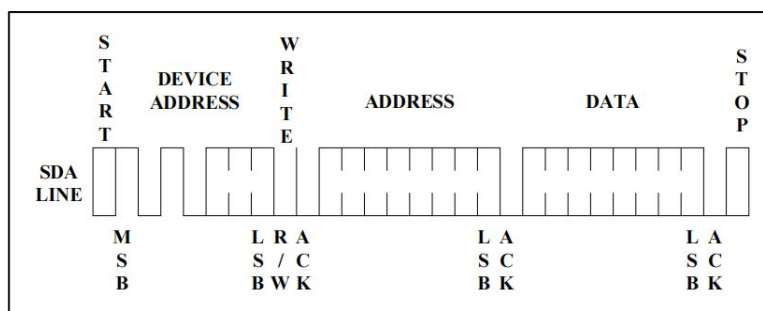


Figure 7. Byte Write



PAGE WRITE: The 2K EEPROM is capable of a 16-byte page write. A page write is initiated the same as a byte write, but the microcontroller does not send a stop condition after the first data word is clocked in. Instead, after the EEPROM acknowledges receipt of the first data word, the microcontroller can transmit up to fifteen more data words. The EEPROM will respond with a "0" after each data word received. The microcontroller must terminate the page write sequence with a stop condition (see **Figure 8**).

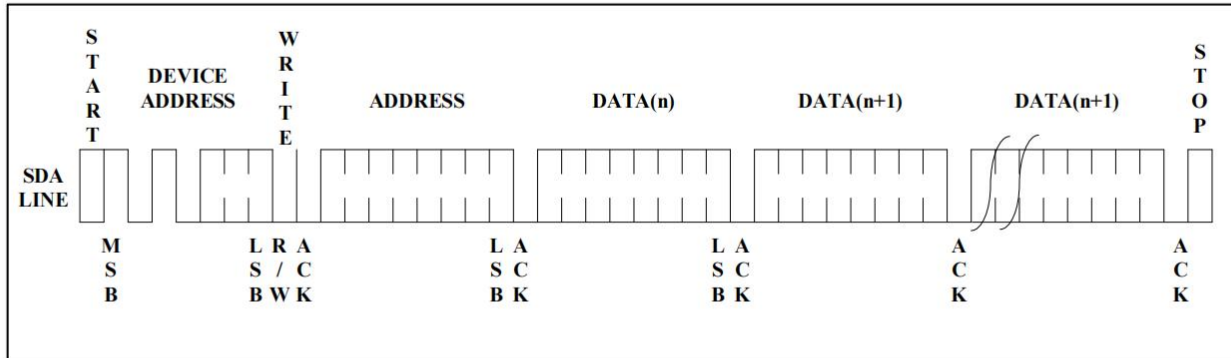


Figure 8. Page Write

The data word address lower four bits are internally incremented following the receipt of each data word. The higher data word address bits are not incremented, retaining the memory page row location. When the word address, internally generated, reaches the page boundary, the following byte is placed at the beginning of the same page. If more than sixteen data words are transmitted to the EEPROM, the data word address will "roll over" and previous data will be overwritten.

ACKNOWLEDGE POLLING: Once the internally timed write cycle has started and the EEPROM inputs are disabled, acknowledge polling can be initiated. This involves sending a start condition followed by the device address word. The read/write bit is representative of the operation desired. Only if the internal write cycle has completed will the EEPROM respond with a "0", allowing the read or write sequence to continue.



5. Read Operations

Read operations are initiated the same way as write operations with the exception that the read/write select bit in the device address word is set to "1". There are three read operations: current address read, random address read and sequential read.

CURRENT ADDRESS READ: The internal data word address counter maintains the last address accessed during the last read or write operation, incremented by one. This address stays valid between operations as long as the chip power is maintained. The address "roll over" during read is from the last byte of the last memory page to the first byte of the first page. The address "roll over" during write is from the last byte of the current page to the first byte of the same page. Once the device address with the read/write select bit set to "1" is clocked in and acknowledged by the EEPROM, the current address data word is serially clocked out. The microcontroller does not respond with an input "0" but does generate a following stop condition (see **Figure 9**).

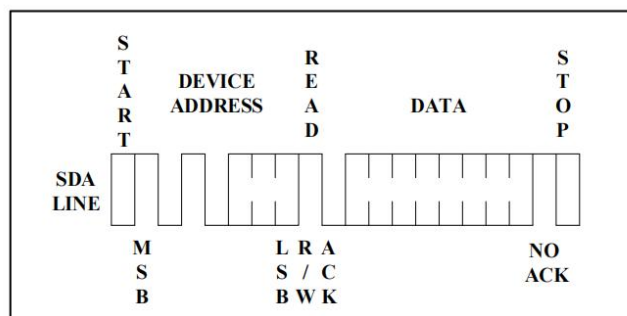


Figure 9. Current Address Read

RANDOM READ: A random read requires a "dummy" byte write sequence to load in the data word address. Once the device address word and data word address are clocked in and acknowledged by the EEPROM, the microcontroller must generate another start condition. The microcontroller now initiates a current address read by sending a device address with the read/write select bit high. The EEPROM acknowledges the device address and serially clocks out the data word. The microcontroller does not respond with a "0" but does generate a following stop condition (see **Figure 10**).

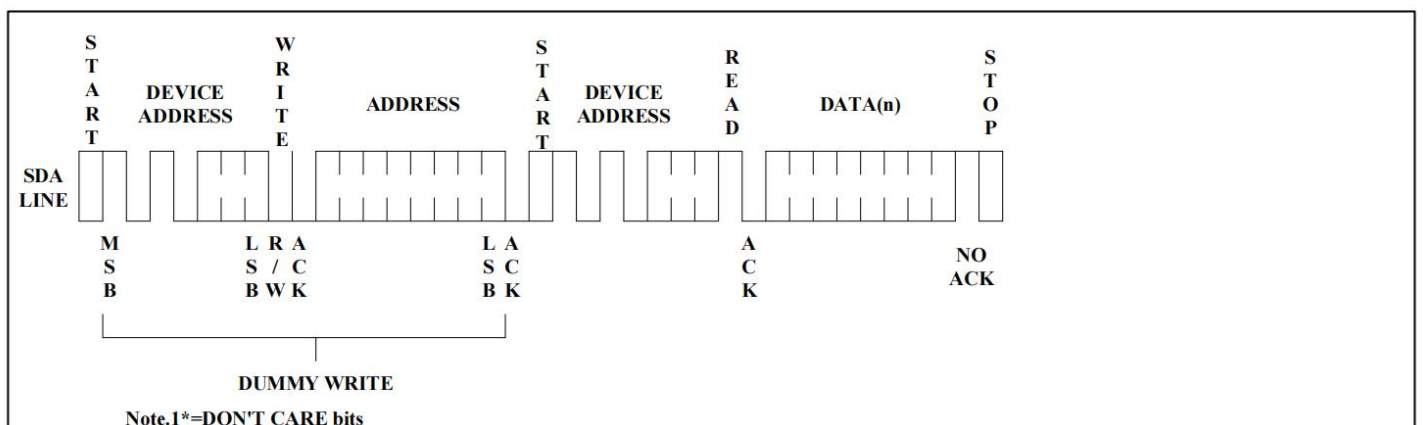


Figure 10. Random Read



Electrical Characteristics

Absolute Maximum Stress Ratings:

- DC Supply Voltage -0.3V to +6.5V
- Input / Output Voltage GND-0.3V to VCC+0.3V
- Storage Temperature -65°C to +150°C
- Electrostatic pulse (Human Body model) 6000V

Comments:

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to this device. These are stress ratings only. Functional operation of this device at these or any other conditions above those indicated in the operational sections of this specification is not implied or intended. Exposure to the absolute maximum rating conditions for extended periods may affect device reliability.

DC Electrical Characteristics

24C01/24C02	$T_A = -40^{\circ}\text{C}$ to $+85^{\circ}\text{C}$	$V_{CC} = +1.7\text{V}$ to $+5.5\text{V}@400\text{kHz}$ $V_{CC} = +2.5\text{V}$ to $+5.5\text{V}@1\text{MHz}$ $C_L = 100\text{ pF}$				
24C01/24C02 E1	$T_A = -40^{\circ}\text{C}$ to $+105^{\circ}\text{C}$					
24C01/24C02 E0	$T_A = -40^{\circ}\text{C}$ to $+125^{\circ}\text{C}$					
Parameter	Symbol	Min	Typ	Max	Unit	Condition
Supply Voltage	V_{CC1}	1.7	-	5.5	V	@400kHz
Supply Voltage	V_{CC2}	2.5	-	5.5	V	@1MHz
Supply Current $V_{CC}=5.0\text{V}$	I_R	-	0.14	0.3	mA	READ @ 400kHz
Supply Current $V_{CC}=5.0\text{V}$	I_W	-	0.28	0.5	mA	WRITE @ 400kHz
Supply Current $V_{CC}=5.0\text{V}$	I_{SB}	-	0.03	0.5	μA	$V_{IN}=V_{CC}$ or V_{SS}
Input Leakage Current	I_{LI}	-	0.10	1.0	μA	$V_{IN}=V_{CC}$ or V_{SS}
Output Leakage Current	I_{LO}	-	0.05	1.0	μA	$V_{OUT}=V_{CC}$ or V_{SS}
Input Low Level	V_{IL}	-0.3	-	$V_{CC} \times 0.3$	V	$V_{CC}=1.7\text{V}$ to 5.5V
Input High Level	V_{IH}	$V_{CC} \times 0.7$	-	$V_{CC} + 0.3$	V	$V_{CC}=1.7\text{V}$ to 5.5V
Output Low Level $V_{CC}=1.7\text{V}$	V_{OL1}	-	-	0.2	V	$I_{OL}=0.15\text{mA}$
Output Low Level $V_{CC}=5.0\text{V}$	V_{OL2}	-	-	0.4	V	$I_{OL}=3.0\text{mA}$

Table 3

Pin Capacitance

Applicable over recommended operating range from $T_A = 25^{\circ}\text{C}$, $f_{SCL} = 1.0\text{ MHz}$, $V_{CC} = +2.5\text{V}$

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Input/Output Capacitance(SDA)	$C_{I/O}$	-	-	8	pF	$V_{IO}=0\text{V}$
Input Capacitance(A0,A1,A2,SCL)	C_{IN}	-	-	6	pF	$V_{IN}=0\text{V}$

Table 4



AC Electrical Characteristics

Applicable over recommended operating range from (unless otherwise noted):

24C01/24C02	$T_A = -40^{\circ}\text{C to } +85^{\circ}\text{C}$	$V_{CC} = +1.7\text{V to } +5.5\text{V}@400\text{kHz}$ $V_{CC} = +2.5\text{V to } +5.5\text{V}@1\text{MHz}$ $C_L = 100\text{ pF}$		
24C01/24C02 E1	$T_A = -40^{\circ}\text{C to } +105^{\circ}\text{C}$			
24C01/24C02 E0	$T_A = -40^{\circ}\text{C to } +125^{\circ}\text{C}$			
Parameter	Symbol	Min.	Max.	Units
Clock Frequency, SCL	f_{SCL}	-	1000	kHz
Clock Pulse Width Low	t_{LOW}	0.5	-	μs
Clock Pulse Width High	t_{HIGH}	0.26	-	μs
Noise Suppression Time	t_i	-	50	ns
Clock Low to Data Out Valid	t_{AA}	-	0.45	μs
Time the bus must be free before a new transmission can start	t_{BUF}	0.5	-	μs
Start Hold Time	$t_{HD:STA}$	0.26	-	μs
Start Setup Time	$t_{SU:STA}$	0.26	-	μs
Data In Hold Time	$t_{HD:DAT}$	0	-	μs
Data In Setup Time	$t_{SU:DAT}$	50	-	ns
Input Rise Time ^{(1) (2)}	t_R	-	-	ns
Input Fall Time ^{(1) (2)}	t_F	-	-	ns
Stop Setup Time	$t_{SU:STO}$	0.26	-	μs
Data Out Hold Time	t_{DH}	50	-	ns
Write Cycle Time	t_{WR}	-	3	ms
5.0V, 25°C, Byte Mode ⁽¹⁾	Endurance	1M	-	Write Cycle

Table 5

Notes:

1. This parameter is ensured by characterization only.
2. There is no min. or max. values for the input signal rise and fall times. It is however recommended by the I²C specification that the input signal rise and fall times be less than 120 ns when $f_{SCL} < 1\text{ MHz}$, more than 20 ns and less than 300 ns when $f_{SCL} < 400\text{ kHz}$.
3. AC measurement conditions:
 R_L (connects to V_{CC}): 1.3 k Ω
 Input pulse voltages: 0.3 V_{CC} to 0.7 V_{CC}
 Input rise and fall time: 50 ns
 Input and output timing reference voltages: 0.5 V_{CC}
 The value of R_L should be concerned according to the actual loading on the user's system.



(256×8)Bus Timing

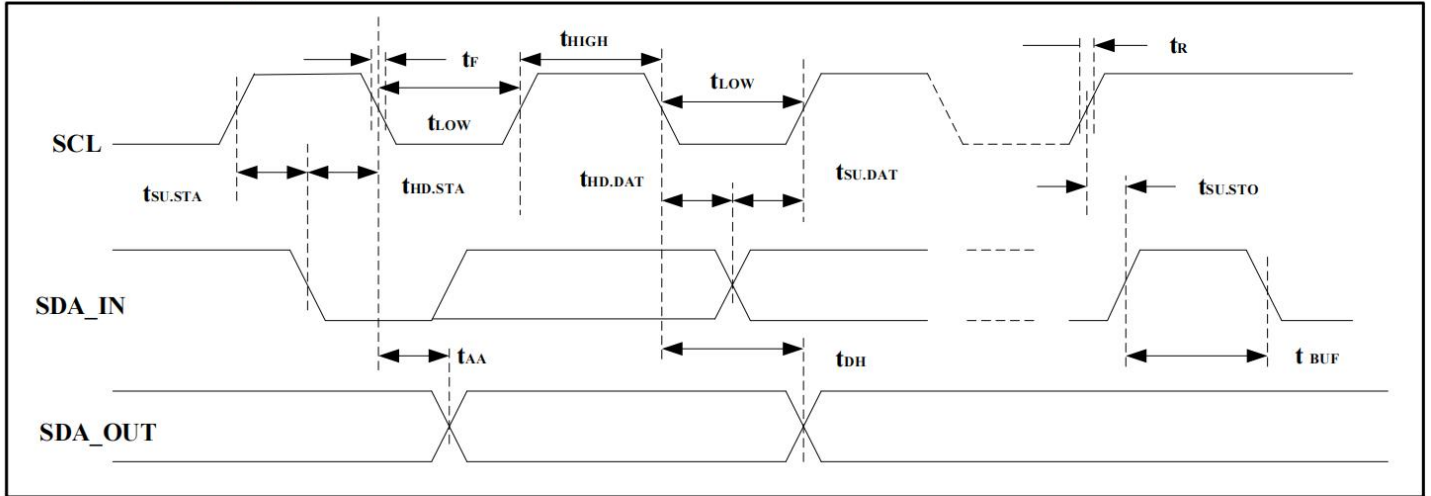


Figure 12. SCL: Serial Clock, SDA: Serial Data I/O

Write Cycle Timing

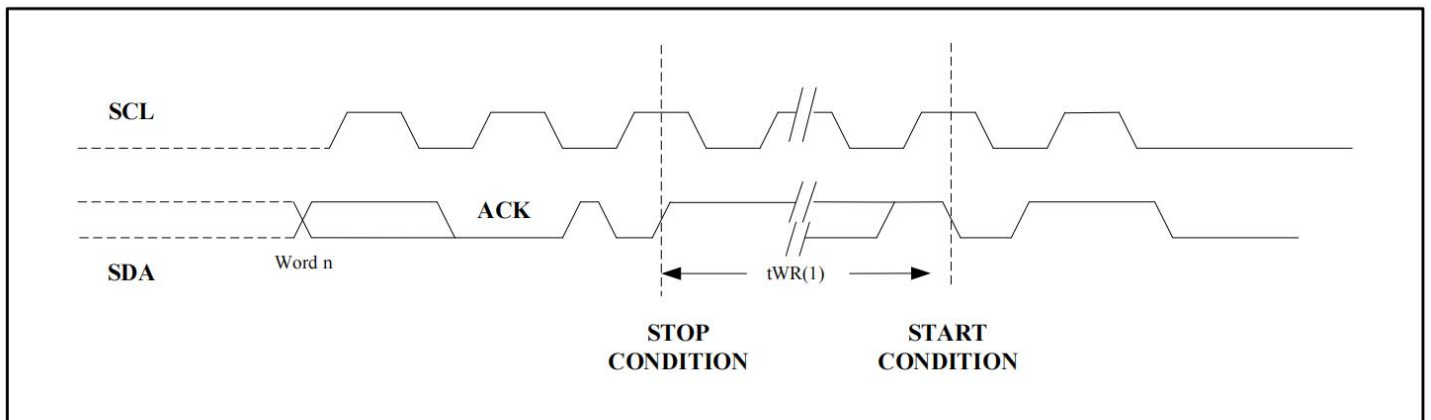
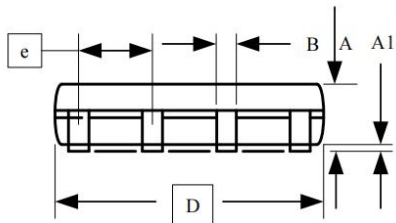
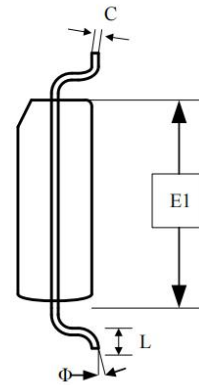
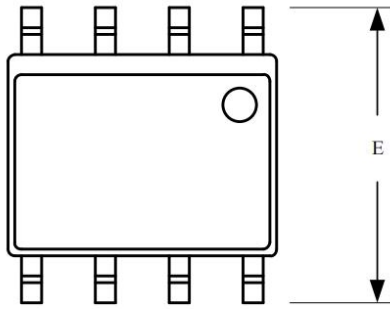


Figure 13. SCL: Serial Clock, SDA: Serial Data I/O



(256×8)Package
InformationSOP

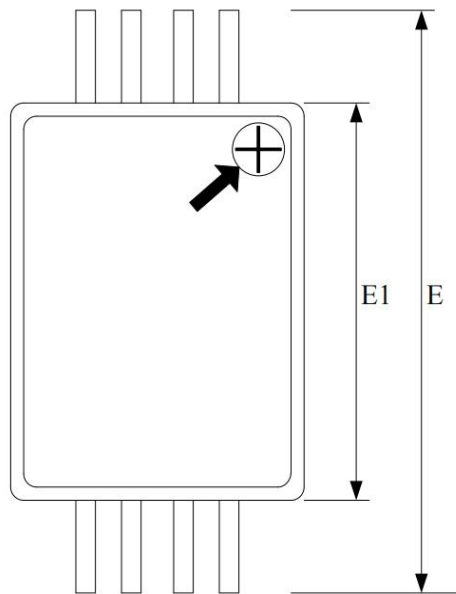


COMMON DIMENSIONS
(Unit of Measure=mm)

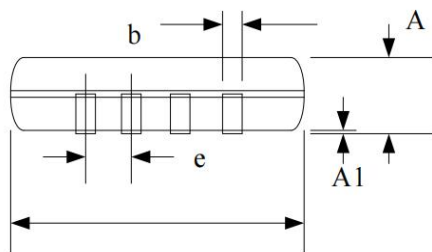
SYMBOL	MIN	NOM	MAX
A	1.35	—	1.75
A1	0.10	—	0.23
B	0.39	—	0.48
C	0.21	—	0.26
D	4.70	4.90	5.10
E1	3.70	3.90	4.10
E	5.80	6.00	6.20
e	1.27BSC		
L	0.50	—	0.80
Φ	0"	—	8"



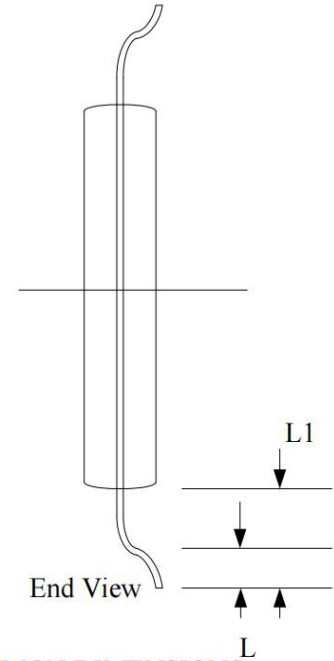
(256×8)TSSOP



Top View



Side View



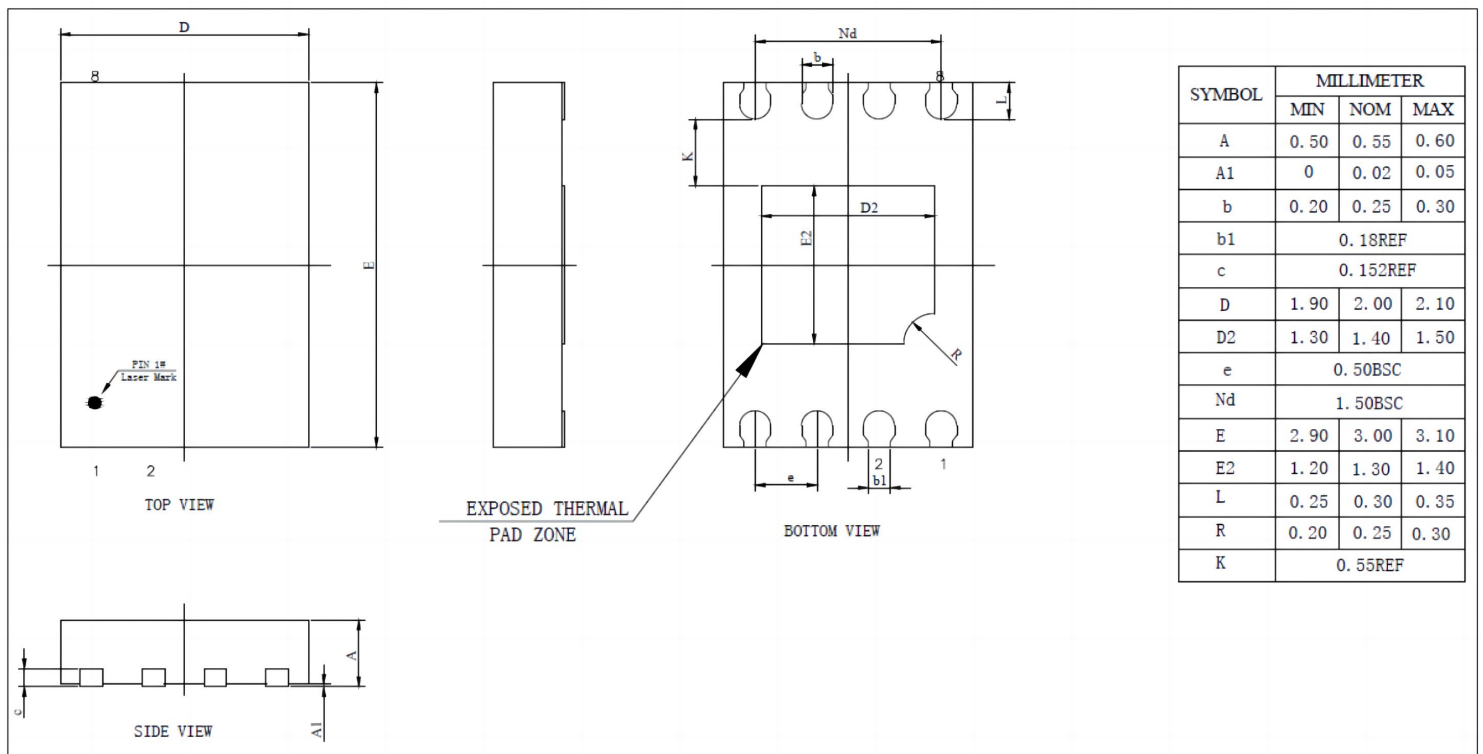
End View

COMMON DIMENSIONS
Unit of Measure=mm

SYMBOL	MIN	NOM	MAX
D	2.90	3.00	3.10
E	6.20	6.40	6.60
E1	4.30	4.40	4.50
A	-	-	1.20
A1	0.05	-	0.15
b	0.21	-	0.30
e	0.65BSC		
L	0.45	0.60	0.75
L1	1.00REF		

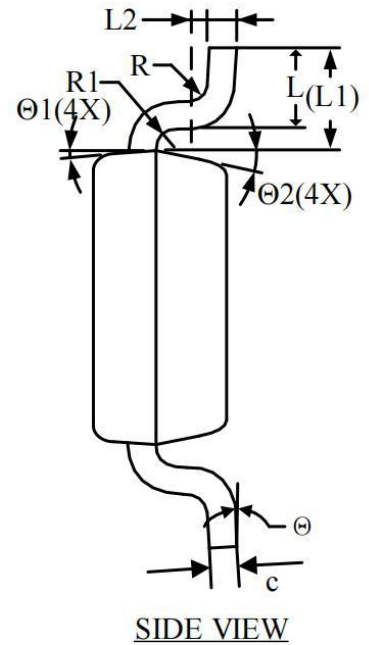
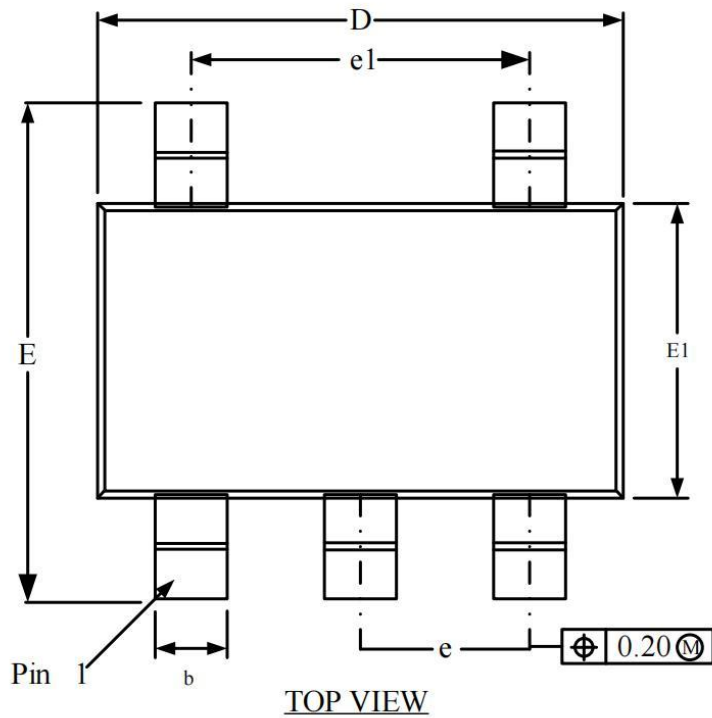


(256×8)UDFN



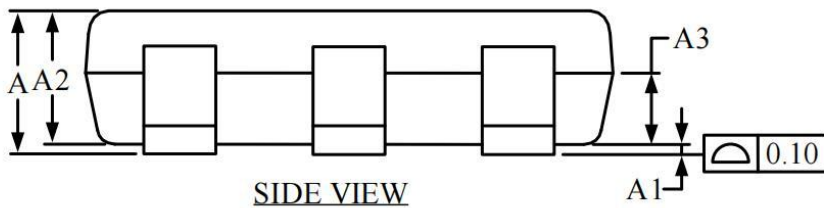


SOT23-5



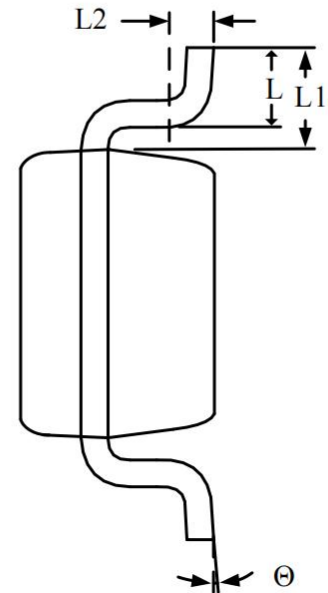
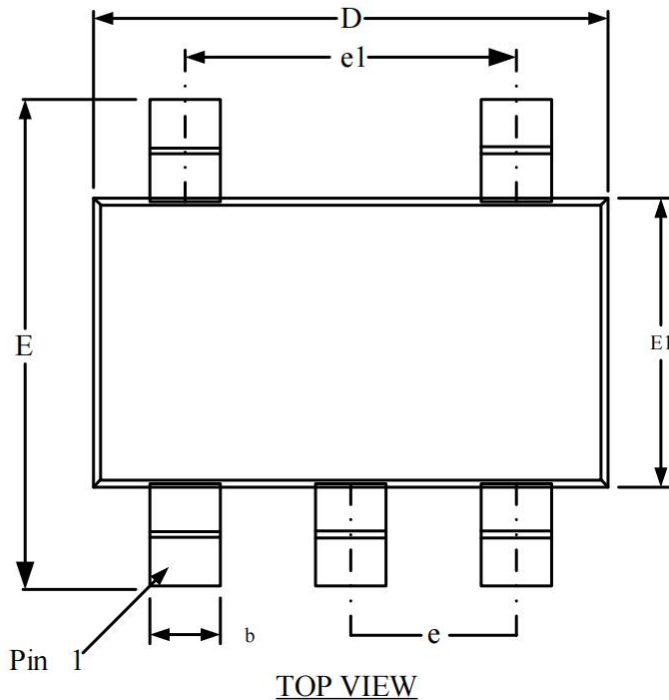
COMMON DIMENSIONS
(UNITS OF MEASURE = MILLIMETER)

SYMBOL	MIN	NOM	MAX
A	—	—	0.90
A1	0.00	—	0.10
A2	0.65	0.75	0.85
A3	0.35	0.40	0.45
b	0.30	0.44	0.50
c	0.14	—	0.20
D	2.85	2.95	3.05
E	2.65	2.80	2.95
E1	1.60	1.65	1.70
e	0.90	0.95	1.00
e1	1.80	1.90	2.00
L	0.30	0.45	0.60
L1	0.575REF		
L2	0.258BSC		
R	—	—	0.25
R1	—	—	0.25
Θ	0°	—	8°
Θ1	3°	5°	7°
Θ2	10°	12°	14°



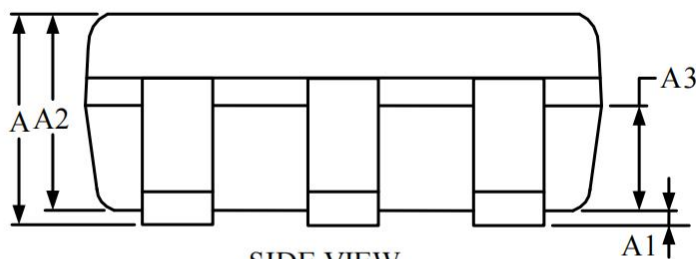


SOT23-5

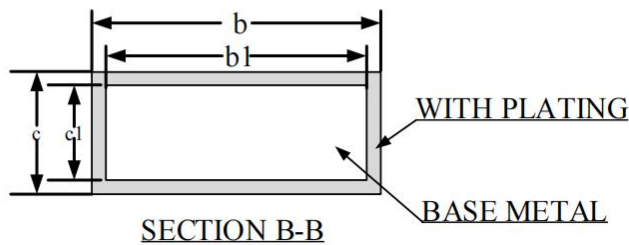


SIDE VIEW

COMMON DIMENSIONS
(UNITS OF MEASURE = MILLIMETER)



SIDE VIEW



SECTION B-B

SYMBOL	MIN	NOM	MAX
A	-	-	1.35
A1	0.04	-	0.15
A2	1.00	1.10	1.20
A3	0.55	0.65	0.75
b	0.38	-	0.48
b1	0.37	0.40	0.43
c	0.11	-	0.21
c1	0.10	0.13	0.16
D	2.72	2.92	3.12
E	2.60	2.80	3.00
E1	1.40	1.60	1.80
e	0.95BSC		
e1	1.90BSC		
L	0.30	-	0.60
L1	0.575REF		
L2	0.258BSC		
Θ	0°	-	8°

Ordering information

Order Number	Package	Package Quantity	Marking On The park
AT24C02C-PUM-TUDI	DIP8	Tube,50,A box of 2000	24C02C



Important statement:

- TUDI Semiconductor reserves the right to modify the product manual without prior notice! Before placing an order, customers need to confirm whether the obtained information is the latest version and verify the completeness of the relevant information.
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